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TABLE OF CONTENTS

SESSION 1 – WELCOME AND PLENARY SESSION

Welcome and Opening Remarks	1
<i>T. Mogami, C. Dennison</i>	
The Systematic Turn in Cognitive Neuroscience	2
<i>K. Mogi</i>	
Device Technology Innovation for Exascale Computing	8
<i>T.C. Chen</i>	

SESSION 2A – STRAIN ENGINEERING

Comparative Study between Si (110) and (100) Substrates on Mobility and Velocity Enhancements for Short-Channel Highly-Strained PFETs	12
<i>S. Mayuzumi, S. Yamakawa, D. Kosemura, M. Takei, K. Nagata, H. Akamatsu, K. Aamari, Y. Tateshita, H. Wakabayashi, M. Tsukamoto, T. Ohno, M. Saitoh, A. Ogura and N. Nagashima</i>	
New Experimental Insight into Ballistic Transport in Strained Bulk MOSFETs	14
<i>D. Fleury, G. Bidal, A. Cros, F. Boeuf, T. Skotnicki and G. Ghibaudo</i>	
Comprehensive Understanding of Surface Roughness Limited Mobility in Unstrained- and Strained-Si MOSFETs by Novel Characterization Scheme of Si/SiO₂ Interface Roughness	16
<i>Y. Zhao, H. Matsumoto, T. Sato, S. Koyama, M. Takenaka and S. Takagi</i>	
Analyses and Optimization of Strained-SiGe on Si pMOSFETs by Using Full-Band Device Simulation	18
<i>H. Takeda, M. Kawada, K. Takeuchi and M. Hane</i>	

SESSION 2B – RESISTANCE MEMORY

Cross-Point Phase Change Memory with 4F² Cell Size Driven by Low-Contact-Resistivity Poly-Si Diode	20
<i>Y. Sasago, M. Kinoshita, T. Morikawa, K. Kurotsuchi, S. Hanzawa, T. Mine, A. Shima, Y. Fujisaki, H. Kume, H. Moriya, N. Takaura and K. Torii</i>	
Vertical Cross-Point Resistance Change Memory for Ultra-High Density Non-Volatile Memory Applications	22
<i>H.S. Yoon, I.-G. Baek, J. Zhao, H. Sim, M.Y. Park, H. Lee, G.-H. Oh, J.C. Shin, I.-S. Yeo and U.-I. Chung</i>	
NiO Resistance Change Memory with a Novel Structure for 3D Integration and Improved Confinement of Conduction Path	24
<i>B. Lee and H.-S.P. Wong</i>	
Oxide-Based RRAM: Uniformity Improvement Using a New Material-Oriented Methodology	26
<i>B. Gao, H.W. Zhang, S. Yu, B. Sun, L.F. Liu, X.Y. Liu, Y. Wang, R.Q. Han, J.F. Kang, B. Yu and Y.Y. Wang</i>	

SESSION 3A – ADVANCED GATE STACK

Gate First High-k/Metal Gate Stacks with Zero SiO_x Interface Achieving EOT=0.59nm for 16nm Application	28
<i>J. Huang, D. Heh, P. Sivasubramani, P.D. Kirsch, G. Bersuker, D.C. Gilmer, M.A. Quevedo-Lopez, M.M. Hussain, P. Majhi, P. Lysaght, H. Park, N. Goel, C. Young, C.S. Park, C. Park, M. Cruz, V. Diaz, P.Y. Hung, J. Price, H.-H. Tseng and R. Jammey</i>	
Cost-Effective 28-nm LSTP CMOS Using Gate-First Metal Gate/High-k Technology	30
<i>T. Tomimatsu, Y. Goto, H. Kato, M. Amma, M. Igarashi, Y. Kusakabe, M. Takeuchi, S. Ohbayashi, S.Sakashita, T. Kawahara, M. Mizutani, M. Inoue, M. Sawada, Y. Kawasaki, S. Yamanari, Y. Miyagawa, Y. Takeshima, Y. Yamamoto, S. Endo, T. Hayashi, Y. Nishida,</i>	
Optimized Ultra-Low Thermal Budget Process Flow for Advanced High-K / Metal Gate First CMOS Using Laser-Annealing Technology	32
<i>C. Ortoland, L.-Å. Ragnarsson, P. Favia, O. Richard, C. Kerner, T. Chiarella, E. Rosseel, Y. Okuno, A. Akheyar, J. Tseng, J.-L. Everaert, T. Schram, S. Kubicek, M. Aoulaiche, M.J. Cho, P.P. Absil, S. Biesemans and T. Hoffmann</i>	

Impact of Area Scaling on Threshold Voltage Lowering in La-Containing High-k/Metal Gate NMOSFETs Fabricated on (100) and (110)Si	34
<i>M. Inoue, Y. Satoh, M. Kadoshima, S. Sakashita, T. Kawahara, M. Anma, R. Nakagawa, H. Umeda, S. Matsuyama, H. Fujimoto and H. Miyatake</i>	
pFET V_t Control with HfO₂/TiN/Poly-Si Gate Stack Using a Lateral Oxygenation Process	36
<i>E. Cartier, M. Steen, B.P. Linder, T. Ando, R. Iijima, M. Frank, J.S. Newbury, Y.H. Kim, F.R. McFeely, M. Copel, R. Haight, C. Choi, A. Callegari, V.K. Paruchuri and V. Narayanan</i>	

SESSION 3B – RANDOM TELEGRAPH NOISE AND SHOT NOISE

New Insights into Oxide Traps Characterization in Gate-All-Around Nanowire Transistors with TiN Metal Gates Based on Combined I_g-I_d RTS Technique	38
<i>L. Zhang, J. Zhuge, R. Wang, R. Huang, C. Liu, D. Wu, Z. Kang, D.-W. Kim, D. Park and Y. Wang</i>	
The First Observation of Shot Noise Characteristics in 10-nm Scale MOSFETs.....	40
<i>J. Jeon, J. Lee, J. Kim, C.H. Park, H. Lee, H. Oh, H.-K. Kang, B.-G. Park and H. Shin</i>	
Increasing Threshold Voltage Variation Due to Random Telegraph Noise in FETs as Gate Lengths Scale to 20 nm	42
<i>N. Tega, H. Miki, F. Pagette, D.J. Frank, A. Ray, M.J. Rooks, W. Haensch and K. Torii</i>	
A New Observation of Strain-Induced Slow Traps in Advanced CMOS Technology with Process-Induced Strain Using Random Telegraph Noise Measurement.....	44
<i>M.H. Lin, E.R. Hsieh, S.S. Chung, C.H. Tsai, P.W. Liu, Y.H. Lin, C.T. Tsai and G.H. Ma</i>	
Single-Charge-Based Modeling of Transistor Characteristics Fluctuations Based on Statistical Measurement of RTN Amplitude	46
<i>K. Takeuchi, T. Nagumo, S. Yokogawa, K. Imai and Y. Hayashi</i>	

SESSION 4A – FOCUS SESSION – 3D SYSTEM INTEGRATION

3D Integration for Energy Efficient System Design.....	48
<i>S. Borkar</i>	
Process-Design Considerations for Three Dimensional Memory Integration	50
<i>S.S. Iyer, T. Kirihaata, M.R. Wordeman, J. Barth, R.H. Hannon and R. Malik</i>	
New 3D Integration Technology and 3D System LSIs	54
<i>M. Koyanagi</i>	
Leading Edge 3D Technology for High Volume Manufacturing	58
<i>S.R. Arkalgud</i>	
TSV and 3D Wafer Bonding Technologies for Advanced Stacking System and Application at ITRI.....	60
<i>W.-C. Lo, Y.-H. Chen, C.-T. Ko and M.-G. Kao</i>	

SESSION 4B – GE MOSFET

V_{th} Variation and Strain Control of High Ge% Thin SiGe Channels by Millisecond Anneal Realizing High Performance pMOSFET beyond 16nm Node	62
<i>S.-H. Lee, J. Huang, P. Majhi, P.D. Kirsch, B.-G. Min, C.-S. Park, J. Oh, W.-Y. Loh, C.-Y. Kang, B. Sassman, P.Y. Hung, S. McCoy, J. Chen, B. Wu, G. Moori, D. Heh, C. Young, G. Bersuker, H.-H. Tseng, S.K. Banerjee and R. Jammy</i>	
High Quality GeO₂/Ge Interface Formed by SPA Radical Oxidation and Uniaxial Stress Engineering for High Performance Ge NMOSFETs.....	64
<i>M. Kobayashi, T. Irisawa, B.M. Kope, Y. Sun, K. Saraswat, H.-S.P. Wong, P. Pianetta and Y. Nishi</i>	
New Approach to Form EOT-Scalable Gate Stack with Strontium Germanide Interlayer for High-k/Ge MISFETs	66
<i>Y. Kamata, A. Takashima, Y. Kamimuta and T. Tezuka, MIRAI-Toshiba and Toshiba</i>	
Physical Origins of Mobility Enhancement of Ge pMISFETs with Si Passivation Layers.....	68
<i>N. Taoka, W. Mizubayashi, Y. Morita, S. Migita, H. Ota and S. Takagi</i>	
Impact of EOT Scaling Down to 0.85nm on 70nm Ge-pFETs Technology with STI.....	70
<i>J. Mitard, C. Shea, B. DeJaeger, A. Pristera, G. Wang, M. Houssa, G. Eneman, G. Hellings, W.-E. Wang, J.C. Lin, F.E. Leys, R. Loo, G. Winderickx, E. Vrancken, A. Stesmans, K. DeMeyer, M. Caymax, L. Pantisano, M. Meuris and M. Heyns</i>	

RUMP SESSIONS

Summary	72
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SESSION 5A – NANOWIRE FETS

High Hole Mobility in Multiple Silicon Nanowire Gate-All-Around pMOSFETs on (110) SOI	74
<i>J. Chen, T. Saraya and T. Hiramoto</i>	
Gate-All-Around Quantum-Wire Field-Effect Transistor with Dopant Segregation at Metal-Semiconductor-Metal Heterostucture	76
<i>H.-S. Wong, L.-H. Tan, L. Chan, G.-Q. Lo, G. Samudra and Y.-C. Yeo</i>	
Sub-10 nm Gate-All-Around CMOS Nanowire Transistors on Bulk Si Substrate	78
<i>M. Li, K.H. Yeo, S.D. Suk, Y.Y. Yeoh, D.-W. Kim, T.Y. Chung, K.S. Oh and W.-S. Lee</i>	
A Novel Thin BOX SOI Technology Using Bulk Si Wafer for System-on-Chip (SoC) Application	80
<i>C.W. Oh, H.J. Bae, J.K. Ha, S.J. Park, B.K. Park, D.-W. Kim, T.Y. Chung, K.S. Oh and W.-S. Lee</i>	

SESSION 5B – SOURCE/DRAIN CONTACT TECHNOLOGY

Selective Phase Modulation of NiSi Using N-ion Implantation for High Performance Dopant-Segregated Source/Drain n-Channel MOSFETs	82
<i>W.-Y. Loh, P.Y. Hung, B.E. Coss, P. Kalra, I. Ok, G. Smith, C.-Y. Kang, S.-H. Lee, J. Oh, B. Sassman, P. Majhi, P. Kirsch, H.-H. Tseng and R. Jammy</i>	
Ultimate Contact Resistance Scaling Enabled by an Accurate Contact Resistivity Extraction Methodology for Sub-20 nm Node	84
<i>H.-N. Lin, W.-W. Hsu, W.-C. Lee and C.H. Wann</i>	
CMOS Band-Edge Schottky Barrier Heights Using Dielectric-Dipole Mitigated (DDM) Metal/Si for Source/Drain Contact Resistance Reduction	86
<i>B.E. Coss, W.-Y. Loh, J. Oh, G. Smith, C. Smith, H. Adhikari, B. Sassman, S. Parthasarathy, J. Barnett, P. Majhi, R.M. Wallace, J. Kim and R. Jammy</i>	
Single Silicide Comprising Nickel-Dysprosium Alloy for Integration in p- and n-FinFETs with Independent Control of Contact Resistance by Aluminum Implant	88
<i>M. Sinha, R.T.P. Lee, S.N. Devi, G.-Q. Lo, E.F. Chor and Y.-C. Yeo</i>	

SESSION 6A – VARIABILITY

Analysis of Extra V_T Variability Sources in NMOS Using Takeuchi Plot	90
<i>T. Tsunomura, A. Nishida, F. Yano, A.T. Putra, K. Takeuchi, S. Inaba, S. Kamohara, K. Terada, T. Mama, T. Hiramoto, and T. Mogami</i>	
Impact of Uniaxial Strain on Channel Backscattering Characteristics and Drain Current Variation for Nanoscale PMOSFETs	92
<i>W. Lee, J.J.-Y. Kuo, W.P.-N. Chen, P. Su and M.-C. Jeng</i>	
Physical Understanding of V_{th} and I_{dsat} Variations in (110) CMOSFETs	94
<i>M. Saitoh, N. Yasutake, Y. Nakabayashi, K. Uchida and T. Numata</i>	
A New Methodology for Evaluating V_T Variability Considering Dopant Depth Profile	96
<i>A.T. Putra, T. Tsunomura, A. Nishida, S. Kamohara, K. Takeuchi, S. Inaba, K. Terada and T. Hiramoto</i>	
Comprehensive Analysis of Variability Sources of FinFET Characteristics	98
<i>T. Matsukawa, S. O'uchi, K. Endo, Y. Ishikawa, H. Yamauchi, Y.X. Liu, J. Tsukada, K. Sakamoto and M. Masahara</i>	

SESSION 6B – SPECIAL SESSION – BEYOND CMOS

A Hybrid CMOS/Magnetic Tunnel Junction Approach for Nonvolatile Integrated Circuits	100
<i>H. Ohno</i>	
Graphene Nanostructures for Device Applications	102
<i>J. Appenzeller, Y. Sui and Z. Chen</i>	
Gate Modulation of Graphene Contacts – on the Scaling of Graphene FETs	105
<i>Z. Chen and J. Appenzeller</i>	
Nonvolatile Solid-Electrolyte Switch Embedded into Cu Interconnect	107
<i>T. Sakamoto, M. Tada, N. Banno, Y. Tsuji, Y. Saitoh, Y. Yabe, H. Hada, N. Iguchi and M. Aono</i>	

Collective-Effect State Variables for Post-CMOS Logic Applications	109
<i>A. Chen, A.P. Jacob, C.Y. Sung, K.L. Wang, A. Khitun and W. Porod</i>	

SESSION 7 – HIGHLIGHTS

Pipe-Shaped BiCS Flash Memory with 16 Stacked Layers and Multi-Level-Cell Operation for Ultra High Density Storage Devices	111
<i>R. Katsumata, M. Kito, Y. Fukuzumi, M. Kido, H. Tanaka, Y. Komori, M. Ishiduki, J. Matsunami, T. Fujiwara, Y. Nagata, L. Zhang, Y. Iwata, R. Kirisawa, H. Aochi and A. Nitayama</i>	
Extremely Scaled Gate-First High-k/Metal Gate Stack with EOT of 0.55 nm Using Novel Interfacial Layer Scavenging Techniques for 22nm Technology Node and Beyond	113
<i>K. Choi, H. Jagannathan, C. Choi, L. Edge, T. Ando, M. Frank, P. Jamison, M. Wang, E. Cartier, S. Zafar, J. Bruley, A. Kerber, B. Linder, A. Callegari, Q. Yang, S. Brown, J. Stathis, J. Iacononi, V. Paruchuri and V. Narayanan</i>	
High Performance 32nm SOI CMOS with High-k/Metal Gate and 0.149μm^2 SRAM and Ultra Low-k Back End with Eleven Levels of Copper	115
<i>B. Greene, Q. Liang, K. Amarnath, Y. Wang, J. Schaeffer, M. Cai, Y. Liang, S. Saroop, J. Cheng, A. Rotondaro, S. J. Han, R. Mo, K. McStay, S. Ku, R. Pal, M. Kumar, B. Dirahoui, B. Yang, F. Tamweber, W-H. Lee, M. Steigerwalt, H. Weijtmans, J. Holt, L. Bl</i>	
Characteristics of sub 5nm Tri-Gate Nanowire MOSFETs with Single and Poly Si Channels in SOI Structure	117
<i>S.D. Suk, M. Li, Y.Y. Yeoh, K.H. Yeo, J.K. Ha, H. Lim, H.W. Park, D.-W. Kim, T.Y. Chung, K.S. Oh and W.-S. Lee</i>	

SESSION 8A – VARIABILITY II

Comprehensive Design Methodology of Dopant Profile to Suppress Gate-LER-Induced Threshold Voltage Variability in 20nm NMOSFETs	119
<i>H. Fukutome, Y. Hori, L. Sponton, K. Hosaka, Y. Momiya, S. Satoh, R. Gull, W. Fichtner and T. Sugii</i>	
Post-Fabrication Self-Convergence Scheme for Suppressing Variability in SRAM Cells and Logic Transistors	121
<i>M. Suzuki, T. Saraya, K. Shimizu, T. Sakurai and T. Hiramoto</i>	
Low Voltage ($V_{\text{ad}}=0.6$ V) SRAM Operation Achieved by Reduced Threshold Voltage Variability in SOTB (Silicon on Thin BOX)	123
<i>R. Tsuchiya, N. Sugii, T. Ishigaki, Y. Morita, H. Yoshimoto, K. Torii and S. Kimura</i>	
Reduction of RTA-Driven Intra-Die Variation via Model-Based Layout Optimization	125
<i>J.C. Scott, O. Gluschenkov, B. Goplen, H. Landis, E. Nowak, F. Clougherty, A. Mocuta, T. Hook, N. Zamdmer, C.W. Lai, M. Eller, D. Chidambarao, J. Yu, P. Chang, J. Ferris, S. Deshpande, Y. Li, H. Shang, G. Hefferon, R. Divakaruni, E. Crabbé and X. Chen</i>	

SESSION 8B – ADVANCED SOURCE/DRAIN ENGINEERING

Sophisticated Methodology of Dummy Pattern Generation for Suppressing Dislocation Induced Contact Misalignment on Flash Lamp Annealed eSiGe Wafer	127
<i>O. Fujii, T. Sanuki, Y. Oshiki, T. Itani, T. Kugimiya, N. Nakamura, M. Tamura, T. Sato, I. Mizushima, H. Yoshimura, M. Iwai and F. Matsuoka</i>	
Design of High-Performance and Highly Reliable nMOSFETs with Embedded Si:C S/D Extension Stressor(Si:C S/D-E)	129
<i>S.S. Chung, E.R. Hsieh, P.W. Liu, W.T. Chiang, S.H. Tsai, T.L. Tsai, R.M. Huang, C.H. Tsai, W.Y. Teng, C.I. Li, T.F. Kuo, Y.R. Wang, C.L. Yang, C.T. Tsai, G.H. Ma, S.C. Chien and S.W. Sun</i>	
26 nm Gate Length CMOSFETs with Aggressively Reduced Silicide Position by Using Carbon Cluster Co-Implanted Raised Source/Drain Extension Structure	131
<i>K. Yako, T. Yamamoto, K. Uejima, T. Hase and M. Hane</i>	
The Fabrication of Low Leakage Junction with Ultra Shallow Profile by the Combination Annealing of 10-ms Low Power and 2-ms High Power FLA	133
<i>T. Onizawa, S. Kato, T. Aoyama, K. Ikeda and Y. Ohji</i>	

SESSION 9A – PROCESS TECHNOLOGY

GeOI and SOI 3D Monolithic Cell Integrations for High Density Applications	135
<i>P. Batude, M. Vinet, A. Pouydebasque, C. Le Royer, B. Previtali, C. Tabone, L. Clavelier, S. Michaud, A. Valentian, O. Thomas, O. Rozeau, P. Coudrain, C. Leyris, K. Romanjek, X. Garros, L. Sanchez, L. Baud, A. Roman, V. Carron, H. Grampeix, E. Augendre</i>	
Scratch-Free Dielectric CMP Slurry with 5-nm Colloidal Ceria Abrasive	137
<i>D. Ryuzaki, Y. Hoshi, Y. Machii, N. Koyama, H. Sakurai and T. Ashizawa</i>	
Reliability of a 300-mm-Compatible 3DI Technology Based on Hybrid Cu-Adhesive Wafer Bonding	139
<i>R.R. Yu, F. Liu, R.J. Polastre, K.-N. Chen, X.H. Liu, L. Shi, E.D. Perfecto, N.R. Klymko, M.S. Chace, T.M. Shaw, D. Dimilia, E.R. Kinser, A.M. Young, S. Purushothaman, S.J. Koester and W. Haensch</i>	
Impact of Backside Cu Contamination in the 3D Integration Process	141
<i>K. Hozawa, K. Takeda and K. Torii</i>	

SESSION 9B – NON-CLASSICAL TRANSISTORS

Programming Characteristics of the Steep Turn-On/Off Feedback FET (FBFET)	143
<i>C.W. Yeung, A. Padilla, T.-J. King Liu and C. Hu</i>	
Germanium-Source Tunnel Field Effect Transistors with Record High I_{ON}/I_{OFF}	145
<i>S.H. Kim, H. Kam, C. Hu and T.-J. King Liu</i>	
Possibilities for $V_{DD} = 0.1V$ Logic Using Carbon-Based Tunneling Field Effect Transistors	147
<i>Y. Gao, T. Low and M. Lundstrom</i>	
A Metallic-CNT-Tolerant Carbon Nanotube Technology Using Asymmetrically-Correlated CNTs (ACCNT)	149
<i>A. Lin, N. Patil, H. Wei, S. Mitra and H.-S.P. Wong</i>	

SESSION 10A – NAND FLASH MEMORY

Novel Vertical-Stacked-Array-Transistor (VSAT) for Ultra-High-Density and Cost-Effective NAND Flash Memory Devices and SSD (Solid State Drive)	151
<i>J. Kim, A.J. Hong, S.M. Kim, E.B. Song, J.H. Park, J. Han, S. Choi, D. Jang, J.-T. Moon and K.L. Wang</i>	
Multi-Layered Vertical Gate NAND Flash Overcoming Stacking Limit for Terabit Density Storage	153
<i>W. Kim, S. Choi, J. Sung, T. Lee, C. Park, H. Ko, J. Jung, I. Yoo and Y. Park</i>	
20nm-Node Planer MONOS Cell Technology for Multi-Level NAND Flash Memory	155
<i>T. Yaegashi, T. Okamura, W. Sakamoto, Y. Matsunaga, T. Toba, K. Sakuma, K. Gomikawa, K. Komiya, H. Nagashima, H. Akahori, K. Sekine, T. Kai, Y. Ozawa, M. Sugi, S. Watanabe, K. Narita, M. Umemura, H. Kutsukake, M. Sakuma, H. Maekawa, Y. Ishibashi, K. Su</i>	
Vertical Cell Array Using TCAT(Terabit Cell Array Transistor) Technology for Ultra High Density NAND Flash Memory	157
<i>J. Jang, H.-S. Kim, W. Cho, H. Cho, J. Kim, S.I. Shim, Y. Jang, J.-H. Jeong, B.-K. Son, D.W. Kim, K. Kim, J.-J. Shim, J.S. Lim, K.-H. Kim, S.Y. Yi, J.-Y. Lim, D. Chung, H.-C. Moon, S. Hwang, J.-W. Lee, Y.-H. Son, U-I. Chung and W.-S. Lee</i>	

SESSION 10B – SPECIAL SESSION – EXPLORATIVE RESEARCH

Guiding Principles Toward Future Gate Stacks Given by the Construction of New Physical Concepts	159
<i>K. Shiraishi</i>	
Applications of Advanced Transmission Electron Microscopy Techniques in Gate Stack Scaling	161
<i>S. Stemmer, J.M. LeBeau, J. Cagnon, Y. Hwang and R. Engel-Herbert</i>	
Charged Defects Reduction in Gate Insulator with Multivalent Materials	163
<i>M. Kouda, N. Umezawa, K. Kakushima, P. Ahmet, K. Shiraishi, T. Chikyow, K. Yamada and H. Iwai</i>	
Correlation Among Crystal Defects, Depletion Regions and Junction Leakage in Sub-30-nm Gate-Length MOSFETs: Direct Examinations by Electron Holography	165
<i>N. Ikarashi, K. Yako, K. Uejima, T. Yamamoto, T. Ikezawa and M. Hane</i>	
A Direct Observation on the Structure Evolution of Memory-Switching Phenomena Using In-Situ TEM	167
<i>D. Cha, S.J. Ahn, S.Y. Park, H. Horii, D.H. Kim, Y.K. Kim, S.O. Park, U I. Jung, M.J. Kim and J. Kim</i>	

SESSION 11A – CMOS DEVICE INTEGRATION

A Scalable and Highly Manufacturable Single Metal Gate/High-k CMOS Integration for Sub-32nm Technology for LSTP Applications	169
<i>C.S. Park, M.M. Hussain, J. Huang, C. Park, K. Tateiwa, C. Young, H.K. Park, M. Cruz, D. Gilmer, K. Rader, J. Price, P. Lysaght, D. Heh, G. Bersuker, P.D. Kirsch, H.-H. Tseng and R. Jammy</i>	
A Highly Manufacturable 28nm CMOS Low Power Platform Technology with Fully Functional 64Mb SRAM Using Dual/Triple Gate Oxide Process	171
<i>S.-Y. Wu, J.J. Liaw, C.Y. Lin, M.C. Chiang, C.K. Yang, J.Y. Cheng, M.H. Tsai, M.Y. Liu, P.H. Wu, C.H. Chang, L.C. Hu, C.I. Lin, H.F. Chen, S.Y. Chang, S.H. Wang, P.Y. Tong, Y.L. Hsieh, K.H. Pan, C.H. Hsieh, C.H. Chen, C.H. Yao, C.C. Chen, T.L. Lee, C.W.</i>	
Fully Depleted Extremely Thin SOI Technology Fabricated by a Novel Integration Scheme Featuring Implant-Free, Zero-Silicon-Loss, and Faceted Raised Source/Drain	173
<i>K. Cheng, A. Khakifirooz, P. Kulkarni, S. Kanakasabapathy, S. Schmitz, A. Reznicek, T. Adam, Y. Zhu, J. Li, J. Faltermier, T. Furukawa, L.F. Edge, B. Haran, S.-C. Seo, P. Jamison, J. Holt, X. Li, R. Loesing, Z. Zhu, R. Johnson, A. Upham, T. Levin, M.</i>	
The Study of Mobility-T_{inv} Trade-Off in Deeply Scaled High-k / Metal Gate Devices and Scaling Design Guideline for 22nm-Node Generation	175
<i>M. Goto, S. Kawanaka, S. Inumiya, N. Kusunoki, M. Saitoh, K. Tsumura, A. Kinoshita, S. Inaba and Y. Toyoshima</i>	

SESSION 11B – NOVEL MEMORY

High-Density and High-Speed 128Mb Chain FeRAMTM with SDRAM-Compatible DDR2 Interface	177
<i>Y. Shimojo, A. Konno, J. Nishimura, T. Okada, Y. Yamada, S. Kitazaki, H. Furuhashi, S. Yamazaki, K. Yahashi, K. Tomioka, Y. Minami, H. Kanaya, S. Shuto, K. Yamakawa, T. Ozaki, H. Shiga, T. Miyakawa, S. Shiratake, D. Takashima, I. Kunishima, T. Hamamoto</i>	
Parallel Multi-Confined (PMC) Cell Technology for High Density MLC PRAM	179
<i>G.H. Oh, Y.L. Park, J.I. Lee, D.H. Im, J.S. Bae, D.H. Kim, D.H. Ahn, H. Horii, S.O. Park, H.S. Yoon, I.S. Park, Y.S. Ko, U.-I. Chung and J.T. Moon</i>	
Performance Breakthrough in NOR Flash Memory with Dopant-Segregated Schottky-Barrier (DSSB) SONOS Devices	181
<i>S.-J. Choi, J.-W. Han, S. Kim, D.-I. Moon, M.-G. Jang, J.S. Kim, K.H. Kim, G.S. Lee, J.S. Oh, M.H. Song, Y.C. Park, J.W. Kim and Y.-K. Choi</i>	
A Novel Buried-Channel FinFET BE-SONOS NAND Flash with Improved Memory Window and Cycling Endurance	183
<i>H.-T. Lue, Y.-H. Hsiao, P.-Y. Du, S.-C. Lai, T.-H. Hsu, S.P. Hong, M.T. Wu, F.H. Hsu, N.Z. Lien, C.-P. Lu, J.-Y. Hsieh, L.-W. Yang, T. Yang, K.-C. Chen, K.-Y. Hsieh, R. Liu and C.-Y. Lu</i>	

SESSION 12A – FLOATING BODY DRAM AND MRAM

SPRAM with Large Thermal Stability for High Immunity to Read Disturbance and Long Retention for High-Temperature Operation	185
<i>K. Ono, T. Kawahara, R. Takemura, K. Miura, M. Yamanouchi, J. Hayakawa, K. Ito, H. Takahashi, H. Matsuoka, S. Ikeda and H. Ohno</i>	
Low-Current Perpendicular Domain Wall Motion Cell for Scalable High-Speed MRAM	187
<i>S. Fukami, T. Suzuki, K. Nagahara, N. Ohshima, Y. Ozaki, S. Saito, R. Nebashi, N. Sakimura, H. Honjo, K. Mori, C. Igarashi, S. Miura, N. Ishiwata and T. Sugibayashi</i>	
Highly Scalable Z-RAM with Remarkably Long Data Retention for DRAM Application	189
<i>T.-S. Jang, J.-S. Kim, S.-M. Hwang, Y.-H. Oh, K.-M. Rho, S.-J. Chung, S.-O. Chung, J.-G. Oh, S. Bhardwaj, J. Kwon, D. Kim, M. Nagoga, Y.-T. Kim, S.-Y. Cha, S.-C. Moon, S.-W. Chung, S.-J. Hong and S.-W. Park</i>	

SESSION 12B – HIGH MOBILITY DEVICES

Mechanisms for Low On-State Current of Ge (SiGe) nMOSFETs: A Comparative Study on Gate Stack, Resistance, and Orientation-Dependent Effective Masses	191
<i>J. Oh, I. Ok, C.-Y. Kang, M. Jamil, S.-H. Lee, W.-Y. Loh, J. Huang, B. Sassman, L. Smith, S. Parthasarathy, B.E. Coss, W.-H. Choi, H.-D. Lee, M. Cho, S.K. Banerjee, P. Majhi, P.D. Kirsch, H.-H. Tseng and R. Jammy</i>	
High Velocity Si-Nanodot : A Candidate for SRAM Applications at 16nm Node and Below	193
<i>G. Bidal, F. Boeuf, S. Denorme, N. Loubet, J.L. Huguenin, P. Perreau, D. Fleury, F. Leverd, S. Lagrasta, S. Barnola, T. Salvétat, B. Orlando, R. Beneyton, L. Clement, R. Pantel, S. Monfray, G. Ghibaudo and T. Skotnicki</i>	

High Mobility Metal S/D III-V-On-Insulator MOSFETs on a Si Substrate Using Direct Wafer Bonding	195
<i>M. Yokoyama, T. Yasuda, H. Takagi, H. Yamada, N. Fukuhara, M. Hata, M. Sugiyama, Y. Nakano, M. Takenaka and S. Takagi</i>	
Strained In_{0.53}Ga_{0.47}As n-MOSFETs: Performance Boost with in-situ Doped Lattice-Mismatched Source/Drain Stressors and Interface Engineering	197
<i>H.-C. Chin, X. Gong, X. Liu, Z. Lin and Y.-C. Yeo</i>	
Author Index	